New Jersey Semi-Conductor Products, Inc.

20 STERN AVE. SPRINGFIELD, NEW JERSEY 07081 U.S.A.

JEDEC TYPE # 2N541, 2N542, 2N543

TRANSITRON

ELEPHONE: (973) 376-2922

(212) 227-6005

FAX: (973) 376-8960

1. General Description:

This transistor is a NPN silicon triode transistor designed primarily for low level, IF and RF amplifier applications in the Audio & RF frequency range for industrial service.

11. Mechanical Data:

- A. Outline Drawings
 - 1. Outline is in accordance with TO-5 pkg.
 - 2. Terminal Designation
 - 1. Emitter
 - 2. Base
 - 3. Collector

111. Absolute Maximum Ratings:

A. Maxir	num Tem	perature
----------	---------	----------

1. Storage Temperature	-65°C to 200°C			
2. Lead Temperature, 1/16" ± 1/32" from				
case for 8 seconds			230°C	
B. Maximum Reverse Rating	2N541	2N 542	2N 543	
1. Emitter-base voltage @ 25°C	2V	2V	2V	
2. Collector-base voltage	15V	30V	45V	
3. Collector-emitter voltage	15V	30V	45V	
C. Maximum Current (DC)				
1. Collector Current, I _C	25 ma.			
D.				
1. Maximum Power Dissipation @ 25°C ambient	0.2 watts			

IV. Electrical Characteristics, 25°C:

A. Static Characteristics

2. Derating Factor

		Min.	Max.	
1. Collector Current,	I _{CBO}		0.5 μa.	
Collector Current,	I _{CBO} @ 150°C		50 μ a.	
Collector Voltage,	V _{CB} = Ratings of 111 -B2			
2. Emitter Current,	I _{EBO}		$0.5~\mu a.$	
Emitter Voltage,	V _{EB} = 2V			TO-5 Package
3. DC Saturation Voltage	22		1.5 V	$\frac{9.335}{370}$ OIA
Collector Current	5 ma			0.305 0.335 DIA
Base Current	2,2 ma			



.0012 watts/0C